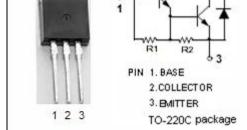


# isc Silicon NPN Darlington Power Transistor

# 2SC1881K

#### **DESCRIPTION**

- · High DC Current Gain-
- : h<sub>FE</sub> = 1000(Min)@ I<sub>C</sub>= 1.5A
- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub> = 60V(Min)
- · Low Collector-Emitter Saturation Voltage-
  - :  $V_{CE(sat)} = 1.2V(Max)@I_{C} = 2.5A$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



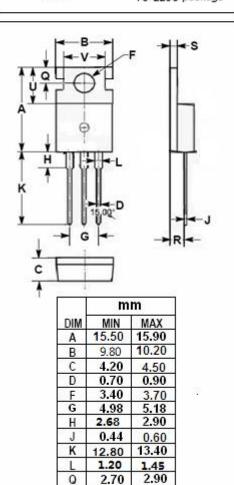


### **APPLICATIONS**

 Designed for High gain amplifier power switching applications.



SYMBOL	PARAMETER	VALUE	UNIT
$V_{\text{CBO}}$	Collector-Base Voltage	60	V
$V_{\text{CEO}}$	Collector-Emitter Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
Ic	Collector Current-Continuous	3	Α
Ісм	Collector Current-Peak	6	Α
P <sub>C</sub>	Collector Power Dissipation $T_C$ =25 $^{\circ}$ C	30	W
T <sub>j</sub>	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C



2.30

1.29 6.45

8.66

S

2.70

6.65

8.86



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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25°C unless otherwise specified

1c=25 C unless otherwise specified									
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 50mA, I <sub>B</sub> = 0	60			V			
V <sub>(BR)EBO</sub>	Emitter –Base Breakdown Voltage	I <sub>C</sub> = 50mA, I <sub>B</sub> = 0	7			V			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2.5A ,I <sub>B</sub> = 20mA			1.2	V			
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 60V, I <sub>E</sub> = 0			0.2	mA			
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 30V, I <sub>B</sub> = 0			0.4	mA			
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1.5A; V <sub>CE</sub> = 1.5V	1000						
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 2.5A; V <sub>CE</sub> = 1.5V	500						
Switching Times									
Ton	Turn on time	$V_{CC} = 11 \text{ V}, I_{C} = 2 \text{ A},$ $I_{B1} = -I_{B2} = 8 \text{ mA}$		1		μS			
Toff	Turn off time			5		μS			

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